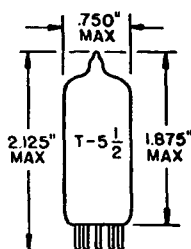


TUNG-SOL

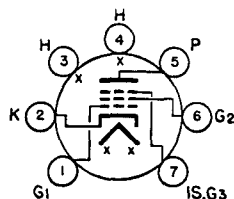
PENTODE

MINIATURE TYPE



GLASS BULB
SMALL-BUTTON
7 PIN BASE E7-1
OUTLINE DRAWING
JEDEC 5-2

SEMIREMOTE-CUTOFF PENTODE
FOR
USE IN THE GAIN-CONTROLLED
PICTURE-IF AMPLIFIER STAGES
OF COLOR T.V. RECEIVERS



BOTTOM VIEW
BASING DIAGRAM
7 CM

THE 6JH6 IS A SEMIREMOTE-CUTOFF PENTODE IN THE 7 PIN MINIATURE CONSTRUCTION. IT IS INTENDED FOR USE IN THE GAIN-CONTROLLED PICTURE-IF AMPLIFIER STAGES OF TELEVISION RECEIVERS. BECAUSE OF ITS CONTROLLED SEMIREMOTE-CUTOFF CHARACTERISTIC, THE 6JH6 CAN SUBSTANTIALLY REDUCE THE EFFECTS OF CROSS MODULATION IN THE IF STAGES OF COLOR T.V. RECEIVERS.

DIRECT INTERELECTRODE CAPACITANCES

	WITHOUT SHIELD	WITH SHIELD NO. 316 CONNECTED TO CATHODE	
GRID 1 TO PLATE	MAX. 0.025	MAX. 0.015	pf
G1 TO (H + K + G2 + G3 + I.S.)	7	7	pf
P TO (H + K + G2 + G3 + I.S.)	2	3	pf

HEATER CHARACTERISTICS AND RATINGS

DESIGN MAXIMUM VALUES - SEE EIA STANDARD RS-239

AVERAGE CHARACTERISTICS	6.3 VOLTS	300	MA.
LIMITS OF APPLIED VOLTAGE		6.3 ± 0.6	VOLTS
PEAK HEATER-CATHODE VOLTAGE:			
HEATER NEGATIVE WITH RESPECT TO CATHODE		200	VOLTS
HEATER POSITIVE WITH RESPECT TO CATHODE		200	VOLTS
DC COMPONENT		100	VOLTS

CONTINUED ON FOLLOWING PAGE

TUNG-SOL

CONTINUED FROM PRECEDING PAGE

MAXIMUM RATINGS

DESIGN MAXIMUM VALUES - SEE EIA STANDARD RS-239

CLASS A1 AMPLIFIER

PLATE VOLTAGE	300	VOLTS
GRID 3 VOLTAGE	0	VOLTS
GRID 2 SUPPLY VOLTAGE	300	VOLTS
GRID 2 VOLTAGE	SEE RATING CHART	
GRID 1 VOLTAGE		
POSITIVE BIAS VALUE	0	VOLTS
GRID 2 INPUT		
FOR GRID 2 VOLTAGES UP TO 150 VOLTS	0.55	VOLTS
FOR GRID 2 VOLTAGES BETWEEN 150 AND 300 VOLTS	SEE RATING CHART	
PLATE DISSIPATION	2.3	WATTS
GRID 1 CIRCUIT RESISTANCE:		
FOR FIXED-BIAS OPERATION	MAX. 0.25	MEGOHM
FOR CATHODE-BIAS OPERATION	MAX. 1	MEGOHM

CHARACTERISTICS

CLASS A1 AMPLIFIER

PLATE VOLTAGE	125	VOLTS
GRID 3 VOLTAGE - CONNECTED TO CATHODE AT SOCKET		
GRID 2 VOLTAGE	125	VOLTS
CATHODE RESISTOR	56	OHMS
PLATE CURRENT	14	MA.
GRID 2 CURRENT	3.6	MA.
TRANSCONDUCTANCE	8,000	μ MHOS
PLATE RESISTANCE	APPROX. 0.26	MEGOHM
GRID 1 VOLTAGE FOR $G_m = 50 \mu$ MHOS	-19	VOLTS
TRANSCONDUCTANCE RANGE AT $E_{C1} = 4.5$ V. AND $R_k = 56 \Omega$	400-900	μ MHOS

